

UTT40N08 Preliminary Power MOSFET

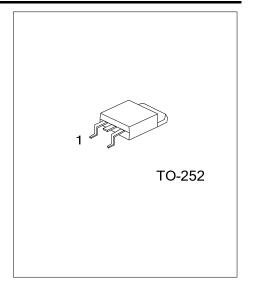
40A, 80V N-CHANNEL POWER MOSFET

■ DESCRIPTION

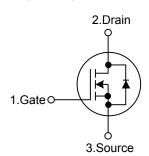
The **UTT40N08** power MOSFET provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness

■ FEATURES

- * $R_{DS(ON)}$ < $45m\Omega$ @ V_{GS} = 10 V
- * Low capacitance
- * Optimized gate charge
- * Fast switching capability
- * Avalanche energy specified



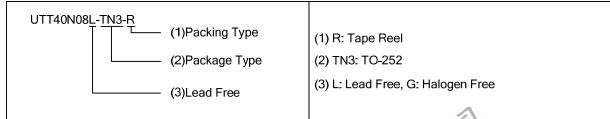
■ SYMBOL



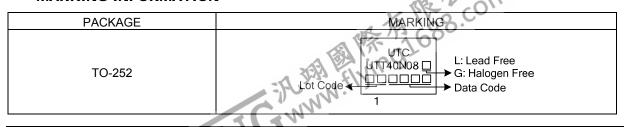
■ ORDERING INFORMATION

Ordering Number		Deelsess	Pin Assignment			De aldes e	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTT40N08L-TN3-R	UTT40N08G-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING INFORMATION



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ABSOLUTE MAXIMUM RATINGS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I _D	40	Α
	Pulsed (Note 1)	I _{DM}	160	Α
Power Dissipation	T _C =25°C	5	65	۱۸/
	T _C =125°C	P_{D}	1.92	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T _{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	62	°C/W	
Junction to Case	θ _{JC}	1.92	°C/W	

ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	80			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =80 V, V _{GS} =0 V, T _J =25°C			1	μΑ
Coto Source Leakage Current Forward	I _{GSS}	V _{GS} =+20V			+100	nA
Gate- Source Leakage Current Reverse		V _{GS} =-20V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$			4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A		35	45	mΩ
DYNAMIC PARAMETERS		,		•		
Input Capacitance	C _{ISS}			2800		pF
Output Capacitance	Coss	V_{DS} =25 V, V_{GS} =0V, f=1.0MHz		320		pF
Reverse Transfer Capacitance	C _{RSS}			140		pF
SWITCHING PARAMETERS		,		•		1
Total Gate Charge	Q_G			200		nC
Gate to Source Charge	Q _{GS}	V_{DS} =25V, V_{GS} =10 V, I_{D} =40A		19		nC
Gate to Drain Charge	Q_{GD}			14		nC
Turn-ON Delay Time	t _{D(ON)}	V _{DS} =30 V, I _D =1 A, V _{GS} =10V,		66	78	ns
Rise Time	t _R			52	70	ns
Turn-OFF Delay Time	t _{D(OFF)}	R _G =1.7 Ω		350	380	ns
Fall-Time	t _F			90	110	ns
SOURCE- DRAIN DIODE RATINGS AND	CHARACTER	RISTICS				
Maximum Body-Diode Continuous Current	Is	$V_D = V_G = 0V$, $V_S = 1.3V$			40	Α
Maximum Body-Diode Pulsed Current	I _{SM}				160	Α
Drain-Source Diode Forward Voltage	V_{SD}	T _J =25°C, I _S =40A, V _{GS} =0V			1.3	V
Notes: 1. Pulse width limited by T _{J(MAX)} 2. Pulse width ≤300us, duty cycle ≤	2%.	T _J =25°C, I _S =40A, V _{GS} =0V	0			
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